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Date: May 2, 2002

*S. McVean*

Sonia V. McVean

PATENT  
36856.599

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Shigeto TAGA U.S. Serial No.: 10/026,811 Filing Date: December 27, 2001 For: SURFACE ACOUSTIC WAVE DEVICE HAVING BUMP ELECTRODES	Art Unit: 2834  Examiner: Unknown
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INFORMATION DISCLOSURE STATEMENT

ASSISTANT COMMISSIONER FOR PATENTS  
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Dear Sir:

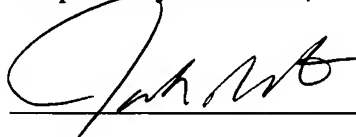
Pursuant to 37 C.F.R. § 1.56, submitted herewith are copies of one (1) reference cited in the enclosed search report issued in a corresponding Japanese patent application. For the Examiner's convenience, we have enclosed an English translation of the Japanese search report and a completed Form PTO-1449. The statement is not a representation that all of the information cited is necessarily effective as prior art against the application.

I hereby state that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign

application not more than 3 months prior to the filing of this statement, and that this is the first citation of these prior art references by a foreign patent office in a counterpart foreign patent application. Accordingly, no fee is necessary for the filing of this statement. Should the Commissioner determine otherwise, the Commissioner is authorized to charge Deposit Account No. 50-1353 for any fee shortages, including the petition fee under 37 C.F.R. § 1.17(p).

Applicant(s) respectfully request(s) that the disclosed reference(s) be made of record in the subject application.

Respectfully submitted,

A handwritten signature in dark ink, appearing to read "Joe Keating", is written over a horizontal line.

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US 6064120 A	20000516	Apparatus and method for face-to-face connection of a die face to a substrate with polymer electrodes	257/780
US 5985486 A	19991116	Electrochemical device	429/188
US 5896081 A	19990420	Resistance temperature detector (RTD) formed with a surface-mount-device (SMD) structure	338/22R
US 5777390 A	19980707	Transparent and opaque metal-semiconductor-metal photodetectors	257/749
US 6137184 A	20001024	Flip-chip type semiconductor device having recessed-protruded electrodes in press-fit contact	257/785
US 6028011 A	20000222	Method of forming electric pad of semiconductor device and method of forming solder bump	438/745
US 5991989 A	19991130	Method of manufacture of surface acoustic wave device	29/25.35
US 5844347 A	19981201	Saw device and its manufacturing method	310/313R
US 5699027 A	19971216	Surface acoustic wave devices having a guard layer	333/193
US 5440125 A	19950808	Radiation detector having a pyroelectric ceramic detection element	250/338.1
US 5108950 A	19920428	Method for forming a bump electrode for a semiconductor device	438/614
US 4692653 A	19870908	Acoustic transducers utilizing ZnO thin film	310/334
US 4259607 A	19810331	Quartz crystal vibrator using Ni-Ag or Cr-Ni-Ag electrode layers	310/364
US 3891873 A	19750624	Piezoelectric resonator with multi layer electrodes	310/364
US 5712523 A	19980127	Surface acoustic wave device	310/313R
US 5325012 A	19940628	Bonded type piezoelectric apparatus, method for manufacturing the same and bonded type piezoelectric element	310/364
US 4736128 A	19880405	Surface acoustic wave device	310/313R
US 4477952 A	19841023	Piezoelectric crystal electrodes and method of manufacture	29/25.35
US 3959747 A	19760525	Metallized lithium niobate and method of making	333/149
US 5746930 A	19980505	Method and structure for forming an array of thermal sensors	216/87
US 6277523 B1	20010821	Electrochemical device	429/304
US 5796205 A	19980818	Surface acoustic wave device and method of producing the same	310/313R
US 5355568 A	19941018	Method of making a surface acoustic wave device	29/25.35
JP 07187894 A	19950725	Ferroelectric thin film for substrate material for functional devices - has metal film(s) provided through amorphous layer on major surface	
US 5643804 A	19970701	Method of manufacturing a hybrid integrated circuit component having a laminated body	438/155
US 5134460 A	19920728	Aluminum bump, reworkable bump, and titanium nitride structure for tab bonding	257/737